

formed and deposited on the wafer, and there is the risk of a lateral misalignment of the photo mask.--

Please insert the following heading before the second full paragraph beginning "It is an object of the present invention to provide a technique for forming insulation . . ." on page 3 of the English translation:

AGTA
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--Brief summary of the invention--

Please replace the second full paragraph on page 3 of the English translation with the following marked-up paragraph:

--When hereby [[.,]]"main process steps" are referred to during the manufacturing process, this is to be understood such that these process steps are emphasized in view of the object and the invention described and claimed herein; however, other processes, such as the integration and the processing of the low voltage elements and the high voltage elements or the etching of the trench structure are not to be excluded.--

Please replace the paragraph bridging pages 3 and 4 of the English translation with the following marked-up paragraph:

--At least one of the existing isolation trenches is provided with insulation layers, which extend as vertical insulation layers into the depth of the trench, thereby reaching to the horizontal (buried) insulation layer. At the same time a horizontal insulation layer is formed on the top of the active semiconductor layer. The fill material has a deep notch or indentation, which is still located above a height level of the horizontal insulation layer. Thus, also a horizontal section of the deposited fill material, which not only fills the isolation trench but is also located above the horizontal insulation layer, also [[to]] forms a fill material layer in this area. Insofar, it may be said more generally that "insulation layers are formed", which comprise horizontal and vertical portions or area sections. Both types of portions are covered by filling the at least one isolation trench.--